

Silicon PNP Epitaxial

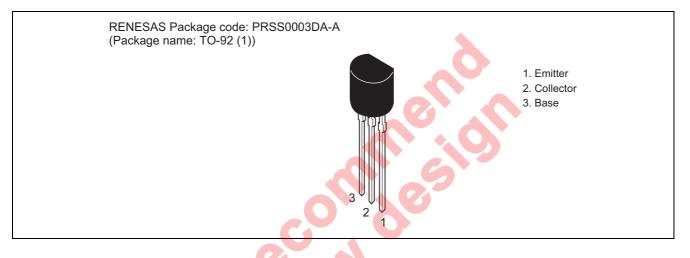
REJ03G0632-0200 (Previous ADE-208-1002) Rev.2.00 Aug.10.2005

Application

• Low frequency high voltage amplifier

• Complementary pair with 2SC1890A

Outline



Absolute Maximum Ratings

		$(Ta = 25^{\circ}C)$		
Item	Symbol	Ratings	Unit	
Collector to base voltage	V _{CBO}	-120	V	
Collector to emitter voltage	V _{CEO}	-120	V	
Emitter to base voltage	V _{EBO}	-5	V	
Collector current	Ι _C	-50	mA	
Collector power dissipation	Pc	300	mW	
Junction temperature	Tj	150	°C	
Storage temperature	Tstg	-55 to +150	°C	



Electrical Characteristics

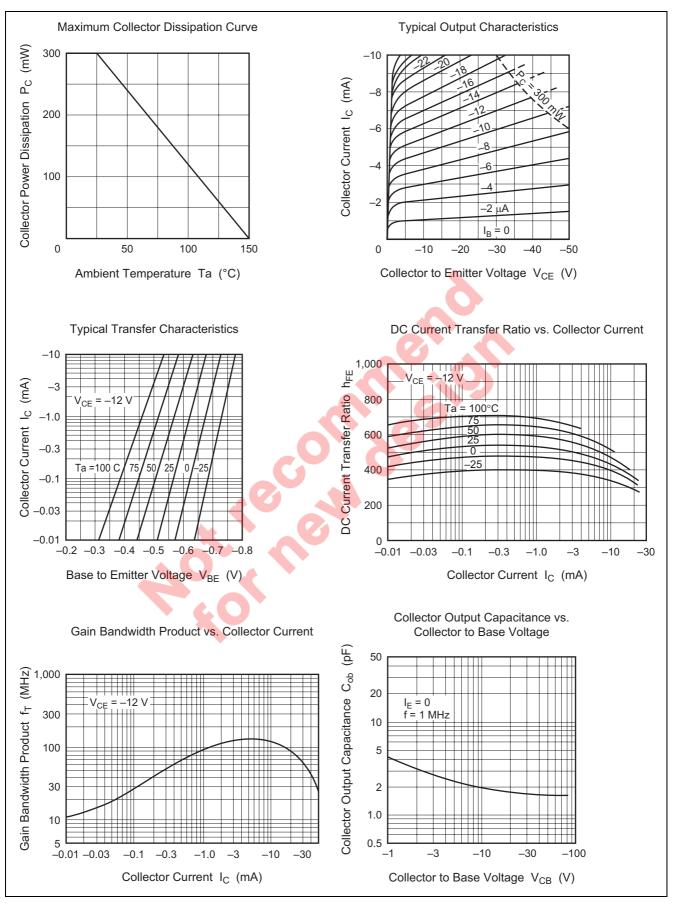
rmbol BR)CEO ICB	Min -120 250 	Typ	Max -0.5 800 -0.75 -0.5 -0.5 -0.5 -10 -10 10	Unit V μA μA V V MHz pF dB	$\label{eq:conditions} \begin{array}{ c c c c } \hline Test \ conditions \\ \hline I_C = -1 \ mA, \ R_{BE} = \infty \\ \hline V_{CB} = -75 \ V, \ I_E = 0 \\ \hline V_{CB} = -100 \ V, \ I_E = 0 \\ \hline V_{CE} = -12 \ V, \\ \hline I_C = -2 \ mA \\ \hline V_{CE} = -12 \ V, \\ \hline I_C = -2 \ mA \\ \hline I_C = -2 \ mA \\ \hline I_C = -2 \ mA \\ \hline I_C = -10 \ mA, \\ \hline I_B = -1 \ mA \\ \hline V_{CE} = -12 \ V, \\ \hline I_C = -2 \ mA \\ \hline V_{CE} = -12 \ V, \\ \hline I_C = -2 \ mA \\ \hline V_{CE} = -12 \ V, \\ \hline I_C = -2 \ mA \\ \hline V_{CE} = -12 \ V, \\ \hline I_C = -2 \ mA \\ \hline V_{CE} = -12 \ V, \\ \hline I_C = -2 \ mA \\ \hline V_{CE} = -12 \ V, \\ \hline I_C = -2 \ mA \\ \hline V_{CE} = -12 \ V, \\ \hline I_C = -2 \ mA \\ \hline V_{CE} = -2 \ mA \\ \hline V_{CB} = -25 \ V, \ I_E = 0, \\ \hline f = 1 \ MHz \\ \hline V_{CE} = -6 \ V, \\ \hline I_C = -50 \ \muA \\ \hline R_g = 50 \ k\Omega, \ f = 1 \ \text{kHz} \\ \end{array}$
I _{CBO} DFE ^{*1} VBE CE(sat) f _T Cob NF s follows.	 250 			μΑ μΑ ν ν ΜΗz pF	$\label{eq:VCB} \begin{split} &V_{CB} = -75 \ V, \ I_E = 0 \\ &V_{CB} = -100 \ V, \ I_E = 0 \\ &V_{CE} = -12 \ V, \\ &I_C = -2 \ mA \\ &V_{CE} = -12 \ V, \\ &I_C = -2 \ mA \\ &I_C = -10 \ mA, \\ &I_B = -1 \ mA \\ &V_{CE} = -12 \ V, \\ &I_C = -2 \ mA \\ &V_{CE} = -12 \ V, \\ &I_C = -2 \ mA \\ &V_{CE} = -25 \ V, \ I_E = 0, \\ &f = 1 \ MHz \\ &V_{CE} = -6 \ V, \\ &I_C = -50 \ \muA \\ \end{split}$
NFE ^{*1} VBE CE(sat) f⊤ Cob NF s follows.	 	 120 1.8	-0.5 800 -0.75 -0.5 	μA V V MHz pF	$\label{eq:VCB} \begin{array}{l} V_{CB} = -100 \ V, \ I_E = 0 \\ V_{CE} = -12 \ V, \\ I_C = -2 \ mA \\ V_{CE} = -12 \ V, \\ I_C = -2 \ mA \\ I_C = -2 \ mA \\ I_C = -10 \ mA, \\ I_B = -1 \ mA \\ V_{CE} = -12 \ V, \\ I_C = -2 \ mA \\ V_{CE} = -25 \ V, \ I_E = 0, \\ f = 1 \ MHz \\ V_{CE} = -6 \ V, \\ I_C = -50 \ \muA \end{array}$
VBE CE(sat) fT Cob NF s follows.		 120 1.8	800 -0.75 -0.5 	V V MHz pF	$V_{CE} = -12 V,$ $I_{C} = -2 mA$ $V_{CE} = -12 V,$ $I_{C} = -2 mA$ $I_{C} = -2 mA$ $I_{C} = -10 mA,$ $I_{B} = -1 mA$ $V_{CE} = -12 V,$ $I_{C} = -2 mA$ $V_{CB} = -25 V,$ $I_{E} = 0,$ $f = 1 MHz$ $V_{CE} = -6 V,$ $I_{C} = -50 \mu A$
VBE CE(sat) fT Cob NF s follows.		1.8	-0.75 -0.5 	V MHz pF	$\begin{split} & I_{C} = -2 \text{ mA} \\ & V_{CE} = -12 \text{ V}, \\ & I_{C} = -2 \text{ mA} \\ & I_{C} = -10 \text{ mA}, \\ & I_{B} = -1 \text{ mA} \\ & V_{CE} = -12 \text{ V}, \\ & I_{C} = -2 \text{ mA} \\ & V_{CB} = -25 \text{ V}, I_{E} = 0, \\ & f = 1 \text{ MHz} \\ & V_{CE} = -6 \text{ V}, \\ & I_{C} = -50 \text{ \muA} \\ \end{split}$
CE(sat) fT Cob NF	-	1.8	-0.5 	V MHz pF	$V_{CE} = -12 V,$ $I_{C} = -2 mA$ $I_{C} = -10 mA,$ $I_{B} = -1 mA$ $V_{CE} = -12 V,$ $I_{C} = -2 mA$ $V_{CB} = -25 V, I_{E} = 0,$ $f = 1 MHz$ $V_{CE} = -6 V,$ $I_{C} = -50 \mu A$
CE(sat) fT Cob NF	-	1.8	-0.5 	V MHz pF	$\begin{split} I_{C} &= -2 \text{ mA} \\ I_{C} &= -10 \text{ mA}, \\ I_{B} &= -1 \text{ mA} \\ V_{CE} &= -12 \text{ V}, \\ I_{C} &= -2 \text{ mA} \\ V_{CB} &= -25 \text{ V}, I_{E} &= 0, \\ f &= 1 \text{ MHz} \\ V_{CE} &= -6 \text{ V}, \\ I_{C} &= -50 \text{ \muA} \end{split}$
f⊤ Cob NF s follows.		1.8	-	MHz pF	$\begin{split} I_{C} &= -10 \text{ mA}, \\ I_{B} &= -1 \text{ mA} \\ V_{CE} &= -12 \text{ V}, \\ I_{C} &= -2 \text{ mA} \\ V_{CB} &= -25 \text{ V}, I_{E} = 0, \\ f &= 1 \text{ MHz} \\ V_{CE} &= -6 \text{ V}, \\ I_{C} &= -50 \text{ \muA} \end{split}$
f⊤ Cob NF s follows.		1.8	-	MHz pF	$\begin{split} I_B &= -1 \text{ mA} \\ V_{CE} &= -12 \text{ V}, \\ I_C &= -2 \text{ mA} \\ V_{CB} &= -25 \text{ V}, I_E = 0, \\ f &= 1 \text{ MHz} \\ V_{CE} &= -6 \text{ V}, \\ I_C &= -50 \text{ \muA} \end{split}$
Cob NF 5 follows.		1.8		pF	$V_{CE} = -12 V,$ $I_{C} = -2 mA$ $V_{CB} = -25 V, I_{E} = 0,$ $f = 1 MHz$ $V_{CE} = -6 V,$ $I_{C} = -50 \mu A$
Cob NF 5 follows.	-	1.8		pF	$\begin{split} I_{C} &= -2 \text{ mA} \\ V_{CB} &= -25 \text{ V}, I_{E} = 0, \\ f &= 1 \text{ MHz} \\ V_{CE} &= -6 \text{ V}, \\ I_{C} &= -50 \text{ \muA} \end{split}$
NF 6 follows.					$V_{CB} = -25 \text{ V}, I_E = 0,$ f = 1 MHz $V_{CE} = -6 \text{ V},$ I_C = -50 μ A
NF 6 follows.					$\label{eq:constraint} \begin{array}{l} f=1 \mbox{ MHz} \\ V_{CE}=-6 \mbox{ V}, \\ I_{C}=-50 \mu A \end{array}$
follows.	 	2	10	dB	$V_{CE} = -6 V,$ $I_{C} = -50 \mu A$
follows.		2	10	dB	$I_C = -50 \ \mu A$
					R _g = 50 kΩ, f = 1 kHz
	on No	8	50		
	C	CON			

D	E	
250 to 500	400 to 800	

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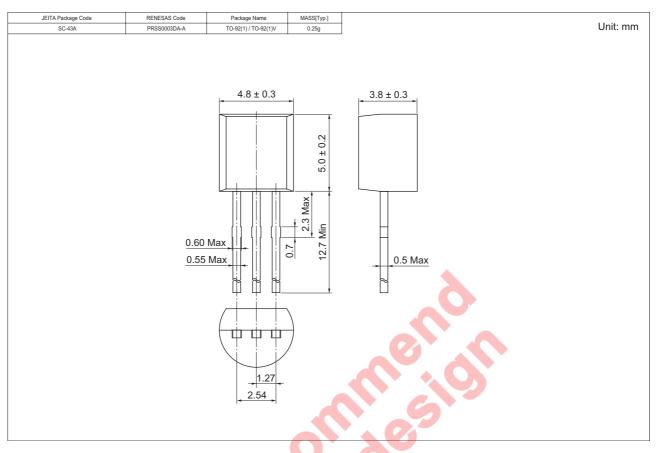


Main Characteristics





Package Dimensions



Ordering Information

Part Name	Quantity	Shipping Container
2SA893ADTZ	2500	Hold Box, Radial Taping
2SA893AETZ		

Note: For some grades, production may be terminated. Please contact the Renesas sales office to check the state of production before ordering the product.



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